

SD101AW...SD101CW

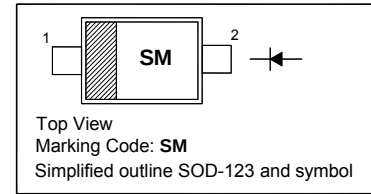
Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

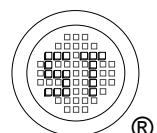


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Peak Repetitive Reverse Voltage	SD101AW SD101BW SD101CW	V_{RRM}	60 50 40	V
Reverse Voltage	SD101AW SD101BW SD101CW	V_R	60 50 40	V
Forward Continuous Current		I_{FM}	15	mA
Power Dissipation		P_d	400	mW
Non-Repetitive Peak Forward Surge Current	at $t = 1\text{ s}$ at $t = 10\text{ }\mu\text{s}$	I_{FSM}	50 2	mA A
Operating and Storage Temperature Range		T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter		Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	SD101AW SD101BW SD101CW	$V_{(BR)R}$	60 50 40	- - -	V
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	SD101AW SD101BW SD101CW SD101AW SD101BW SD101CW	V_F	- - - - - -	0.41 0.4 0.39 1 0.95 0.9	V
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	SD101AW SD101BW SD101CW	I_R	- - -	200 200 200	nA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	SD101AW SD101BW SD101CW	C_T	- - -	2 2.1 2.2	pF
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\text{ }\Omega$		t_{rr}	-	1	ns



Dated : 30/10/2009

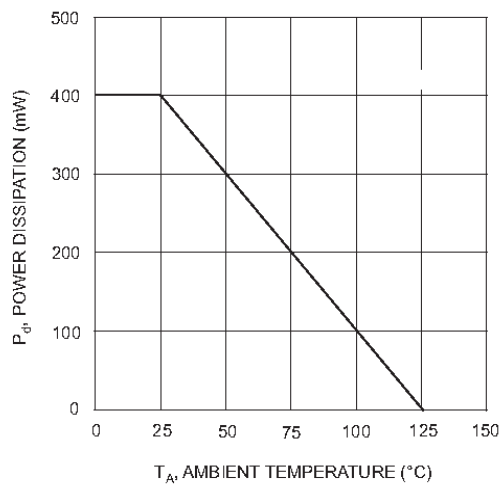


Fig. 1 Power Derating Curve

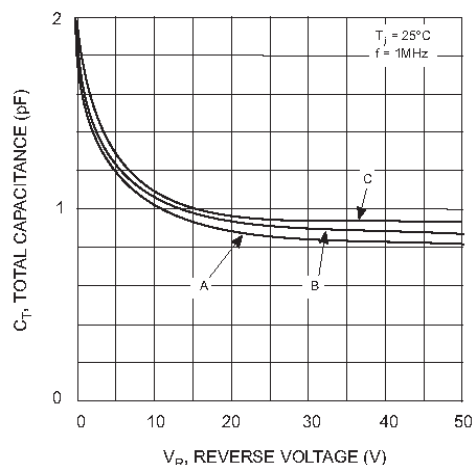


Fig. 3 Typical Total Capacitance vs Reverse Voltage

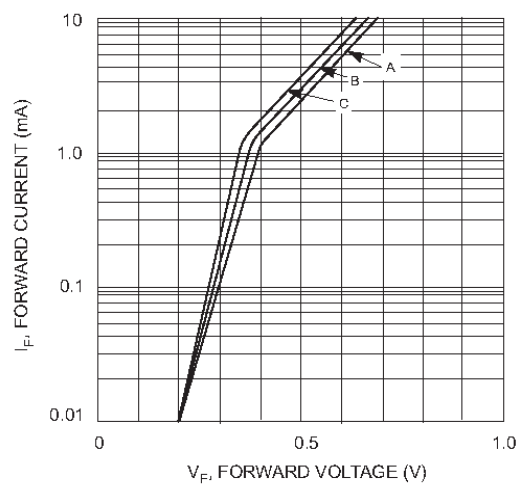


Fig. 2 Typical Forward Characteristic

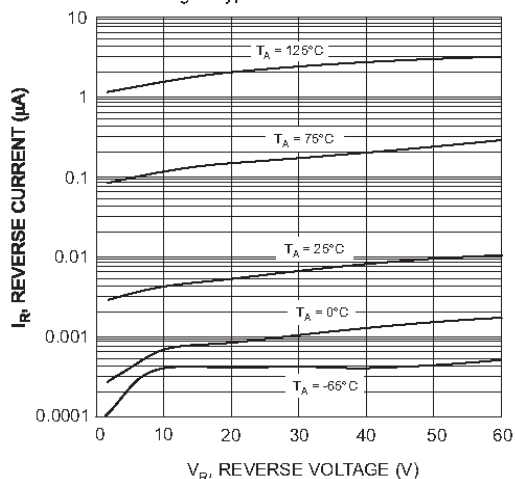
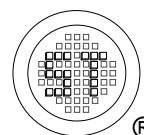


Fig. 4 Typical Reverse Characteristics

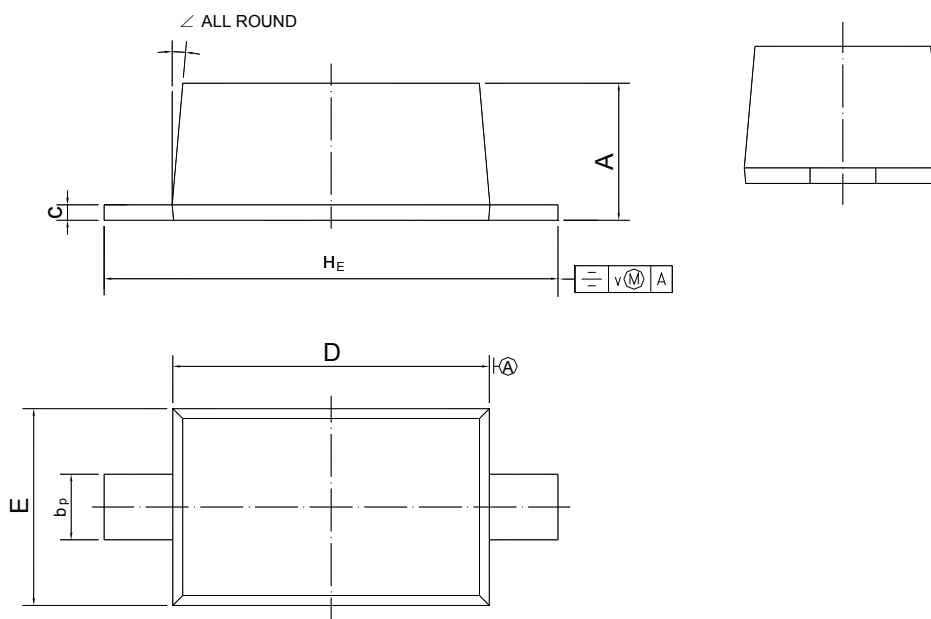


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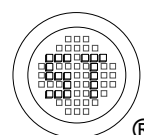
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°



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